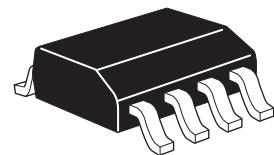


ZXMN6A09DN8

60V SO8 N-channel enhancement mode MOSFET

Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.040 @ $V_{GS} = 10V$	5.6
	0.060 @ $V_{GS} = 4.5V$	4.6

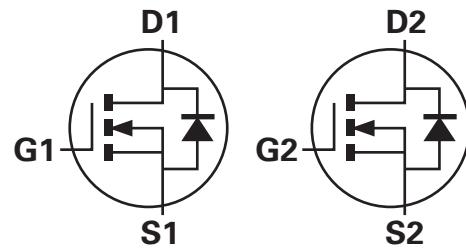


Description

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage power management applications.

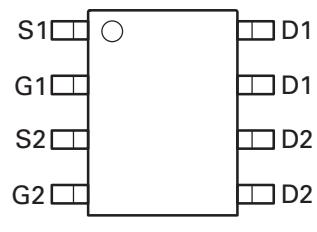
Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOIC package



Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control



Top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A09DN8TA	7	12	500

Device marking

ZXMN
6A09D

ZXMN6A09DN8

Absolute maximum ratings

Thermal resistance

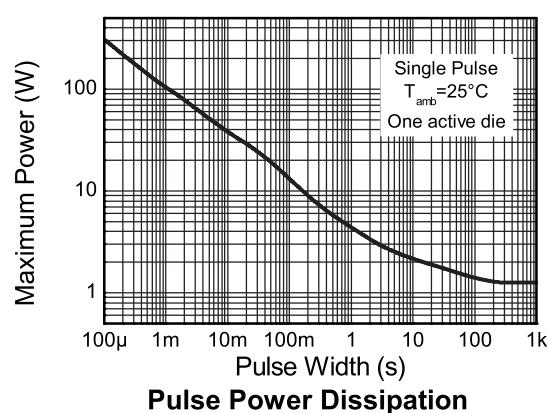
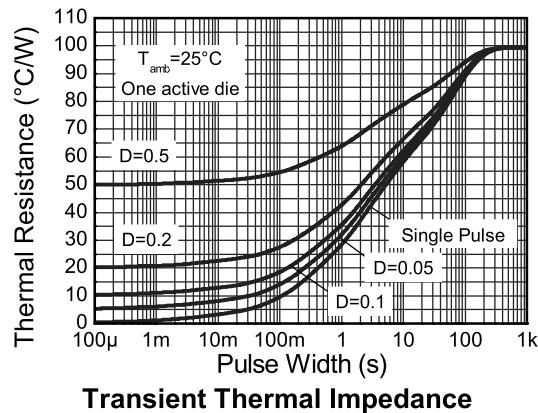
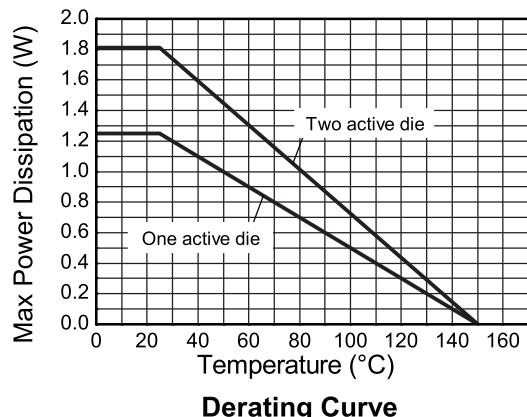
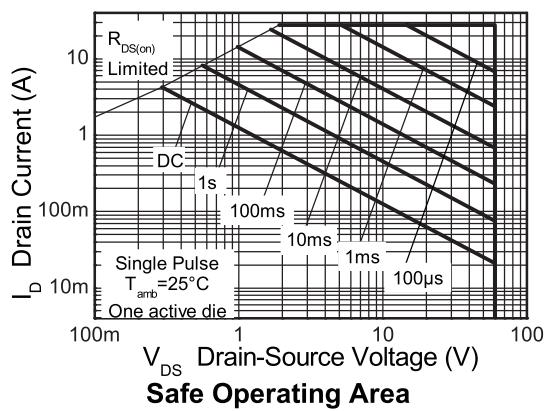
Parameter	Symbol	Limit	Unit
Junction to ambient ^{(a)(d)}	$R_{\theta JA}$	100	°C/W
Junction to ambient ^{(a)(e)}	$R_{\theta JA}$	70	°C/W
Junction to ambient ^{(b)(d)}	$R_{\theta JA}$	60	°C/W

NOTES:

NOTE:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ sec.
- (c) Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width $300\mu\text{s}$ - pulse width limited by maximum junction temperature.
- (d) For a dual device with one active die.
- (e) For a device with two active die running at equal power.

Characteristics



ZXMN6A09DN8

Electrical characteristics (at $T_{amb} = 25^\circ C$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	60			V	$I_D = 250\mu A, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}			1	μA	$V_{DS} = 60V, V_{GS}=0V$
Gate-body leakage	I_{GSS}			100	nA	$V_{GS} = \pm 20V, V_{DS}=0V$
Gate-source threshold voltage	$V_{GS(th)}$	1.0		3.0	V	$I_D = 250\mu A, V_{DS}=V_{GS}$
Static drain-source on-state resistance (*)	$R_{DS(on)}$			0.040	Ω	$V_{GS} = 10V, I_D = 8.2A$
				0.060	Ω	$V_{GS} = 4.5V, I_D = 7.4A$
Forward transconductance ^(*) ([‡])	g_{fs}		15		S	$V_{DS} = 15V, I_D = 8.2A$
Dynamic^(‡)						
Input capacitance	C_{iss}		1407		pF	$V_{DS} = 40V, V_{GS}=0V$ $f=1MHz$
Output capacitance	C_{oss}		121		pF	
Reverse transfer capacitance	C_{rss}		59		pF	
Switching^(†) ([‡])						
Turn-on-delay time	$t_{d(on)}$		4.9		ns	$V_{DD} = 15V, I_D = 3.5A$ $R_G \geq 6.0\Omega, V_{GS} = 10V$
Rise time	t_r		5.0		ns	
Turn-off delay time	$t_{d(off)}$		25.3		ns	
Fall time	t_f		4.6		ns	
Total gate charge	Q_g		12.4		nC	$V_{DS} = 15V, V_{GS} = 5V$ $I_D = 3.5A$
Total gate charge	Q_g		24.2		nC	$V_{DS} = 15V, V_{GS} = 5V$
Gate-source charge	Q_{gs}		5.2		nC	$I_D = 3.5A$
Gate drain charge	Q_{gd}		3.5		nC	
Source-drain diode						
Diode forward voltage ^(*)	V_{SD}		0.85	0.95	V	$T_j = 25^\circ C, I_S = 6.6A,$ $V_{GS}=0V$
Reverse recovery time ^(‡)	t_{rr}		26.3		ns	$T_j = 25^\circ C, I_S = 3.5A,$ $di/dt = 100A/\mu s$
Reverse recovery charge ^(‡)	Q_{rr}		26.6		nC	

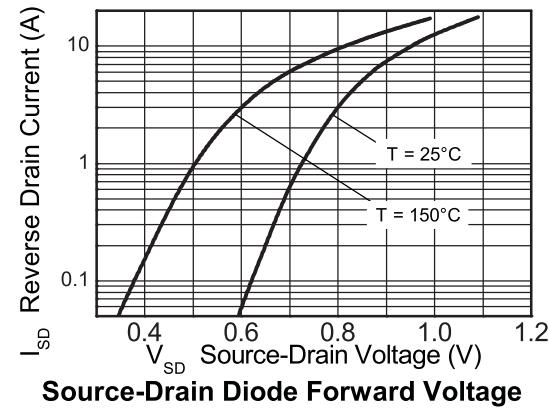
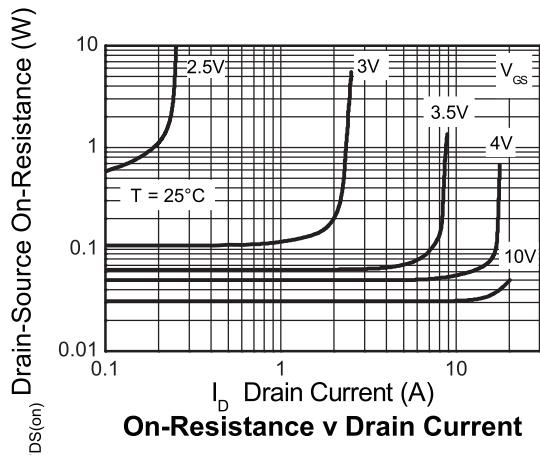
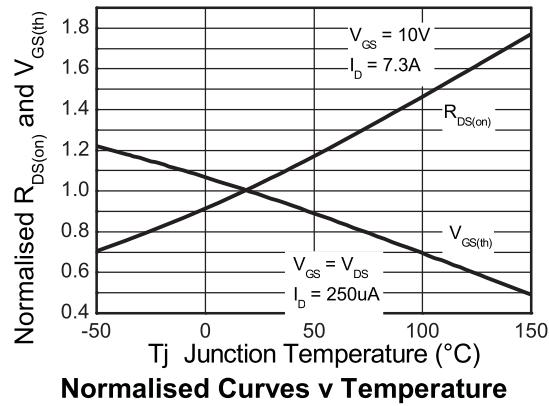
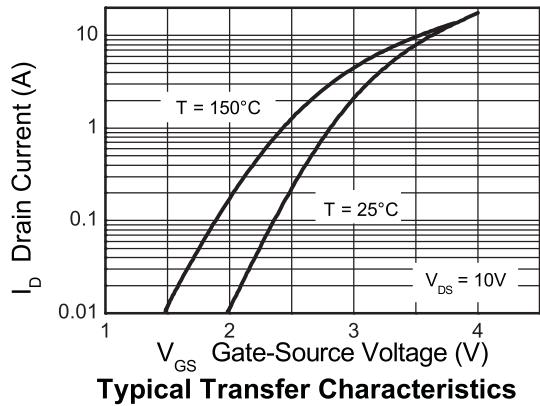
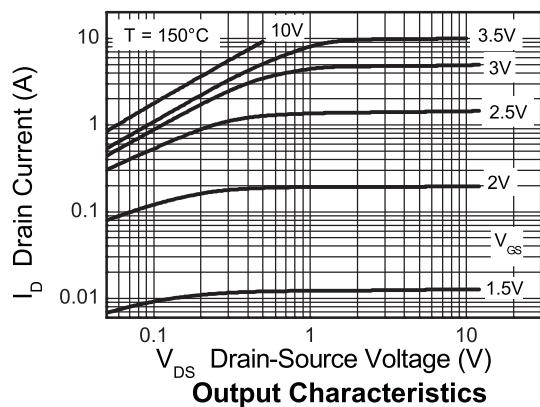
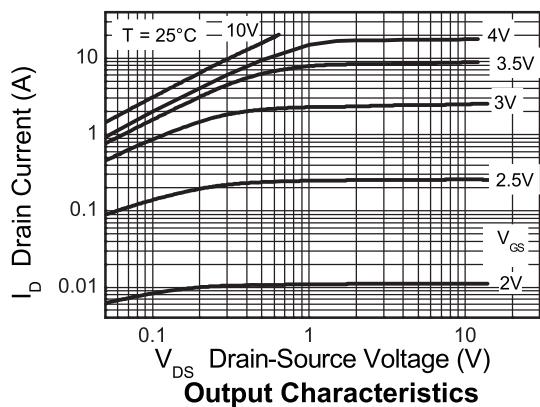
NOTES:

(*) Measured under pulsed conditions. Pulse width ≤ 300 s; duty cycle $\leq 2\%$.

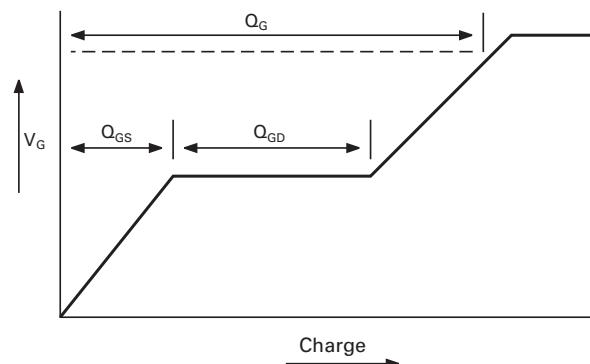
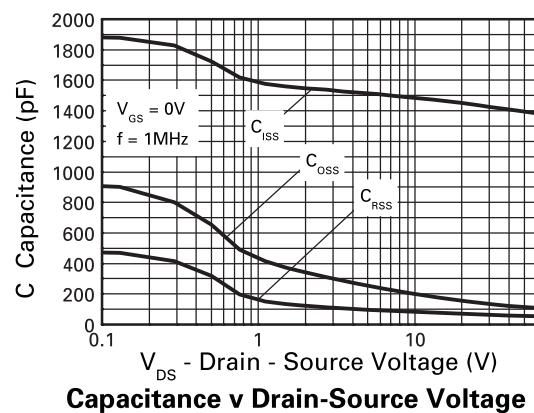
(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

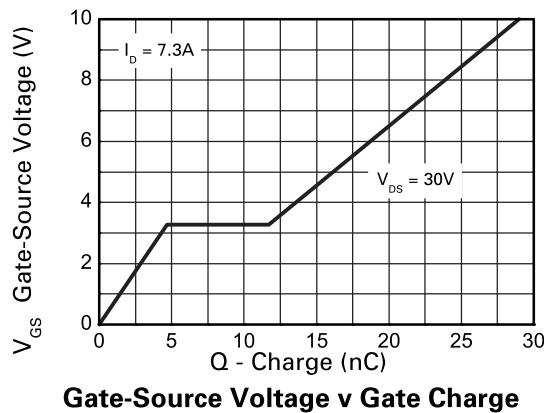
Typical characteristics



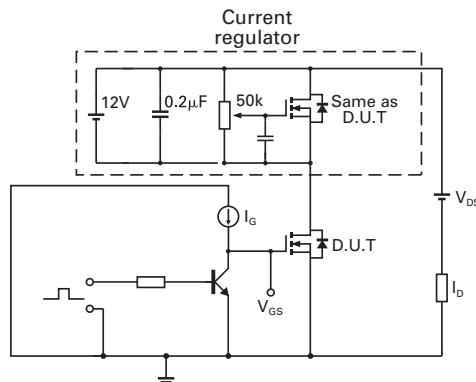
Typical characteristics



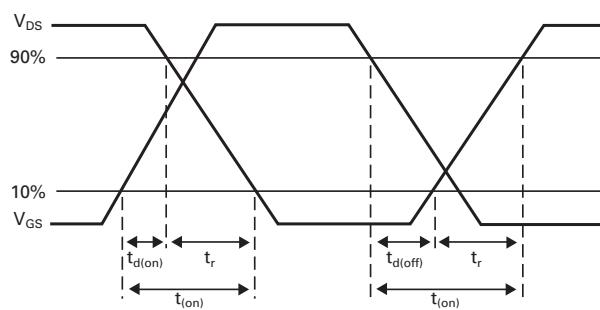
Basic gate charge waveform



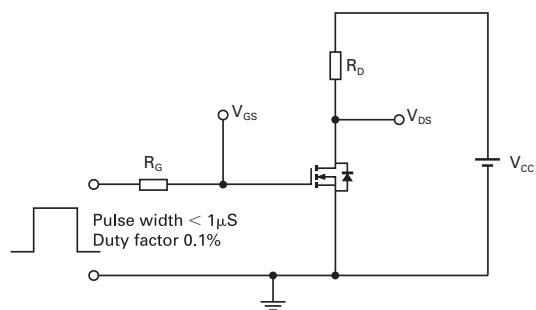
Gate-Source Voltage v Gate Charge



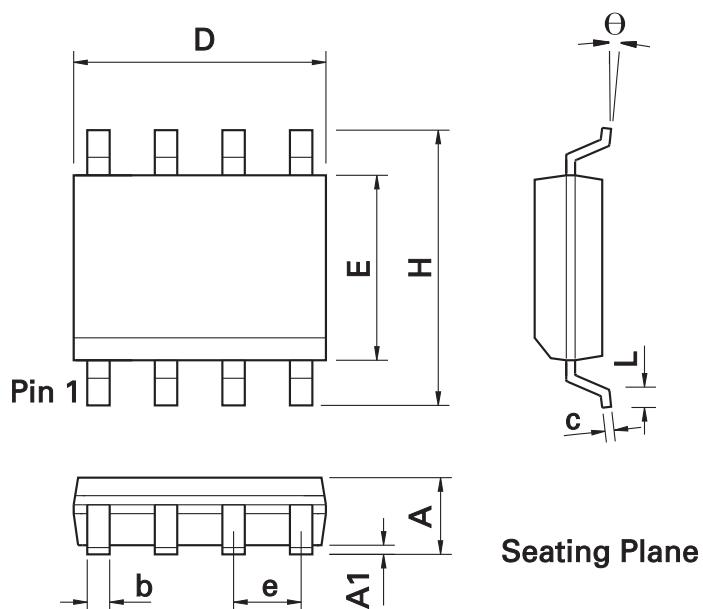
Gate charge test circuit



Switching time waveforms



Switching time test circuit

Package outline - SO8

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	Θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

ZXMIN6A09DN8

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Zetex sales offices

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH	Zetex Inc	Zetex (Asia Ltd)	Zetex Semiconductors plc
Kustermann-park	700 Veterans Memorial Highway	3701-04 Metroplaza Tower 1	Zetex Technology Park, Chadderton
Balanstraße 59	Hauppauge, NY 11788	Hing Fong Road, Kwai Fong	Oldham, OL9 9LL
D-81541 München	USA	Hong Kong	United Kingdom
Germany			
Telefon: (49) 89 45 49 49 0	Telephone: (1) 631 360 2222	Telephone: (852) 26100 611	Telephone: (44) 161 622 4444
Fax: (49) 89 45 49 49 49	Fax: (1) 631 360 8222	Fax: (852) 24250 494	Fax: (44) 161 622 4446
europesales@zetex.com	usa.sales@zetex.com	asia.sales@zetex.com	hq@zetex.com

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